REMARKS

Claims 1, 3-7 and 9-14 are pending in the present application. Claims 1 and 3-7 have been amended. Claims 9-14 have been presented herewith. Claims 2 and 8 have been canceled.

Priority Under 35 U.S.C. 119

Applicant notes the Examiner's acknowledgment of the Claim for Priority under 35 U.S.C. 119, and receipt of the certified copy of the priority document.

Drawings

Applicant notes the Examiner's acceptance of the drawings as filed along with the present application on February 2, 2004.

Claim Rejections-35 U.S.C. 102

Claims 1-8 have been rejected under 35 U.S.C. 102(e) as being anticipated by the Allen et al. reference (U.S. Patent No. 6,560,137). This rejection, insofar as it may pertain to the presently pending claims, is traversed for the following reasons.

The ferroelectric memory device of claim 1 has been amended to include the features of claim 2, including in combination a plurality of judgement word line pairs "each of which is connected to a respective one of the judgement memory cells, and wherein the judgement word lines are of a respective judgement word line pair are

supplied with a common voltage level". Applicant respectfully submits that the Allen et al. reference as relied upon by the Examiner does not disclose these features.

With regard to claim 2, the Examiner has asserted on page 4 of the current Office Action that the Allen et al. reference discloses a plurality of judgement word line pairs WRE and WRO in Figs. 8 and 9, and has further asserted that in view of Figs. 3, 20, 22 and 24 of the Allen et al. reference, lines WRE and WRO are supplied with a common voltage level. Applicant however respectfully submits that the Examiner has misinterpreted the Allen et al. reference.

As described beginning in column 13, line 44 of the Allen et al. reference with respect to Fig. 20, **a representative word line WLO** and a reference word line WRE are activated at time t_1. Thus, contrary to the Examiner's assertion, Fig. 20 of the Allen et al. reference shows that a representative word line WLO and a reference word line WRE appear to have the same voltage level, not that reference word lines WRE and WRO have the same voltage level. Figs. 22 and 24 of the Allen et al. reference similarly fail to show reference word lines WRE and WRO as having a same voltage level, contrary to the assertion by the Examiner.

Moreover, Fig. 3 of the Allen et al. reference as further relied upon by the Examiner shows a word line signal WL and a plate line signal PL. Fig. 3 of the Allen et al. reference as relied upon by the Examiner does not show that reference word lines WRE and WRO, and more particularly does not show reference word lines WRE and WRO as having a same voltage level, contrary to the Examiner's assertion. Applicant

therefore respectfully submits that the ferroelectric memory device of claim 1 distinguishes over the Allen et al. reference as relied upon by the Examiner, and that this rejection of claims 1 and 3-6 is improper for at least these reasons.

The ferroelectric memory device of claim 7 includes in combination a plurality of judgement word line pairs "each of the judgement word line pairs being connected to respective ones of the second ferroelectric memory cells, wherein judgement word lines of a respective judgement word line pair are supplied with a same voltage level".

As noted above, Figs. 3, 20, 22 and 24 of the Allen et al. reference as specifically relied upon by the Examiner, do not disclose reference word lines WRE and WRO as having a same voltage level. The Allen et al. reference as relied upon by the Examiner thus fails to meet the features of claim 7. Applicant therefore respectfully submits that the ferroelectric memory device of claim 7 distinguishes over the Allen et al. reference as relied upon by the Examiner, and that this rejection is improper for at least these reasons.

Claims 1, 3-5 and 7 have been rejected under 35 U.S.C. 102(b) as being anticipated by the Hirano et al. reference (U.S. Patent No. 5,751,628). This rejection, insofar as it may pertain to the presently pending claims, is traversed for the following reasons.

As noted above, claim 1 has been amended to feature in combination that "the judgement word lines of a respective judgement word line pair are supplied with a common voltage". Claim 7 has been amended to feature in combination that

"judgement word lines of a respective judgement word line pair are supplied with a same voltage level". The Hirano et al. reference as relied upon by the Examiner clearly does not disclose these features. Applicant therefore respectfully submits that claims 1, 3-5 and 7 distinguish over the Hirano et al. reference for at least these reasons.

Claims 9-14

The ferroelectric memory of claim 9 includes in combination a memory cell array; a judgement memory cell array; and a plurality of judgement word line pairs "being connected to respectively different ones of the judgement memory cells, and a judgement word lines of respective judgement word line pairs are connected together". The Allen et al. reference in particular does not disclose or even remotely suggest that reference word lines WRE and WRO are connected together, as would be necessary to meet the features of claim 9. Applicant therefore respectfully submits that claims 9-14 distinguish over and would not have been obvious in view of the prior art as relied upon by the Examiner for at least these reasons.

Conclusion

Claims 1 and 7 have been respectively amended to include the features of dependent claims 2 and 8. Claims 1 and 7 are thus of substantively similar scope as previous claims 2 and 8. The remaining claims have been amended merely to improve form, rather than to further distinguish over the relied upon prior art. Accordingly, the

above noted claim amendments should not be construed as narrowing scope within the meaning of *Festo*.

The Examiner is respectfully requested to reconsider and withdraw the corresponding rejections, and to pass the claims of the present application to issue, for at least the above reasons.

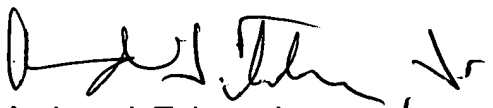
In the event that there are any outstanding matters remaining in the present application, please contact Andrew J. Telesz, Jr. (Reg. No. 33,581) at (571) 283-0720 in the Washington, D.C. area, to discuss these matters.

Pursuant to the provisions of 37 C.F.R. 1.17 and 1.136(a), the Applicant hereby petition for an extension of three (3) months to April 14, 2006, for the period in which to file a response to the outstanding Office Action. The required fee of $1020.00 should be charged to Deposit Account No. 50-0238.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment for any additional fees that may be required, or credit any overpayment, to Deposit Account No. 50-0238.

Respectfully submitted,

VOLENTINE FRANCOS & WHITT, P.L.L.C.



Andrew J. Telesz, Jr.
Registration No. 33,581

Telephone No.: (571) 283-0720
Facsimile No.: (571) 283-0740